



# 제 30회 한국반도체학술대회

The 30th Korean Conference on Semiconductors

2023년 2월 13일(월)~ 15일(수) | 강원도 하이원리조트(그랜드호텔 컨벤션타워)

2023년 2월 15일(수), 16:00-17:45

Room G (스페이드 II+III, 6층)

## K. Memory (Design & Process Technology) 분과 [WG3-K] DRAM, MRAM, and NAND Flash Memory

좌장: 오정훈 마스터(삼성전자), 김성준 교수(동국대학교)

<p><b>WG3-K-1</b> 16:00-16:30 [초청]</p>	<p><b>3D NAND Flash Development Status and Challenges</b> Daewoong Kang <i>Seoul National University</i></p>
<p><b>WG3-K-2</b> 16:30-17:00 [초청]</p>	<p><b>Technology of Cross-point MRAM for High Density Memory</b> 김수길, 서수만, 윤종민, 김세연, 나명희 <i>SK Hynix</i></p>
<p><b>WG3-K-3</b> 17:00-17:15</p>	<p><b>Investigation of Dynamic Negative bias Temperature Instability of 1x-nm DRAM Peripheral PMOS Transistors for Cryogenic Memory Applications</b> Ha Young Bang<sup>1</sup>, Hee Jun Lee<sup>1</sup>, Jingyu Park<sup>1</sup>, Jisook Hong<sup>2</sup>, Seonhaeng Lee<sup>2</sup>, and Dae Hwan Kim<sup>1</sup> <sup>1</sup><i>School of Electrical Engineering, Kookmin University, <sup>2</sup>Memory Division, Samsung Electronics Co., Ltd.</i></p>
<p><b>WG3-K-4</b> 17:15-17:30</p>	<p><b>Random Telegraph Noise-Based Analysis of Electron Traps in the Cryogenic Operation of Sub 30-nm DRAM Cell Array Transistors</b> Sangwon Lee<sup>1</sup>, Ga Won Yang<sup>1</sup>, Sungju Choi<sup>1</sup>, Jisook Hong<sup>2</sup>, Seonhaeng Lee<sup>2</sup>, and Dae Hwan Kim<sup>1</sup> <sup>1</sup><i>School of Electrical Engineering, Kookmin University, <sup>2</sup>Memory Division, Samsung Electronics Co., Ltd.</i></p>
<p><b>WG3-K-5</b> 17:30-17:45</p>	<p><b>Analysis of Mechanical Stress on Charge Trap Nitride (CTN) for Program Operation in 3D NAND Flash Memory</b> Donghyun Kim, Kihoon Nam, Chanyang Park, Giho Yang, Jinsu Jeong, Sanguk Lee, Jaewan Lim, and Rock-Hyun Baek <i>Department of Electrical Engineering, POSTECH</i></p>